

# P-Channel 30-V (D-S) MOSFET

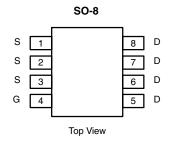
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	
-30 -	$0.02 @ V_{GS} = -10 V$	-8.0	
	0.035 @ V <sub>GS</sub> = -4.5 V	-6.0	

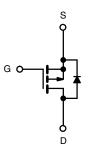
#### FEATURES

 Lead (Pb)-Free Version is RoHS Compliant



RoHS COMPLIANT





P-Channel MOSFET

Si4435DY-T1-A-E3 (Lead (Pb)-Free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 $^{\circ}$ UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V <sub>DS</sub>	-30					
Gate-Source Voltage		V <sub>GS</sub>	±20	V			
	$T_A = 25^{\circ}C$		-8.0				
Continuous Drain Current $(T_J = 150^{\circ}C)^a$	T <sub>A</sub> = 70°C	I <sub>D</sub>	-6.4				
Pulsed Drain Current		I <sub>DM</sub>	-50	— A			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-2.1	$\neg$			
Manimum Davida Diania ati ang	T <sub>A</sub> = 25°C	6	2.5	144			
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70°C	PD	1.6	W			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	50	°C/W	

Notes

a. Surface Mounted on FR4 Board,  $t\,\leq\,$  10 sec.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

Ordering Information: Si4435DY-T1-REV A

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SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit	
Static					•	•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},\ I_D=-250\ \mu A$	-1.0	-2.0	-3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = $\pm 20$ V			±100	nA	
Zana Oata Malta za Duala Orimant		$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		-1			
Zero Gate Voltage Drain Current	IDSS	$V_{DS}$ = –30 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 $^{\circ}C$			-5	μΑ	
		$V_{DS}$ $\leq$ –5 V, $V_{GS}$ = –10 V	-40				
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS}$ $\leq$ –5 V, $V_{GS}$ = –4.5 V	-10			A	
		$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -8.0 \text{ A}$		0.015	0.02	Ω	
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -5.0 \text{ A}$		0.022	0.035		
Forward Transconductance <sup>b</sup>		$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -8.0 \text{ A}$		20		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	$I_{\rm S} = -2.1$ A, $V_{\rm GS} = 0$ V		-0.75	-1.2	V	
Dynamic <sup>a</sup>			•				
Total Gate Charge	Qg			47	60	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, \ V_{GS} = -10 \text{ V}, \ I_D = -4.6 \text{ A}$		9.5			
Gate-Drain Charge	Q <sub>gd</sub>			8			
Gate Resistance	R <sub>G</sub>			2.75	4.1	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	30	ns	
Rise Time	tr	$V_{DD} = -15 \text{ V}, \text{ R}_{L} = 15 \Omega$		17	30		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -1$ Å, $V_{GEN} = -10$ V, $R_G = 6 \Omega$		75	120		
Fall Time	t <sub>f</sub>			31	80		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -2.1 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		40	80	]	

Notes

Guaranteed by design, not subject to production testing. Values shown are for Product Revision A. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. a.

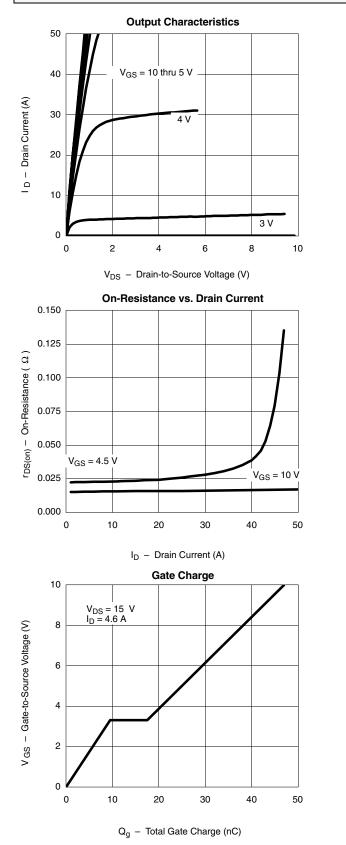
b.

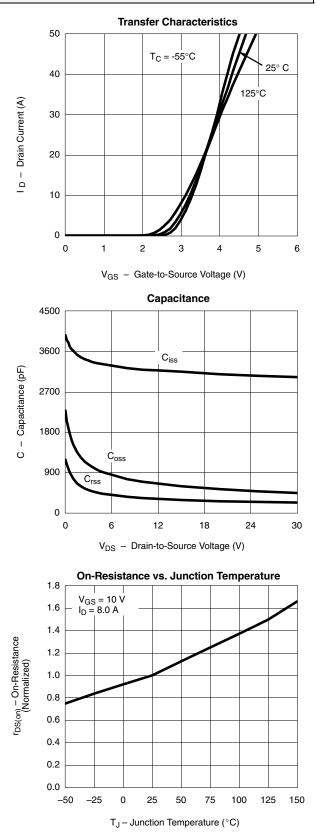
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## Si4435DY Vishay Siliconix

#### TYPICAL CHARACTERISTICS, PRODUCT REVISION A (25°C UNLESS NOTED)



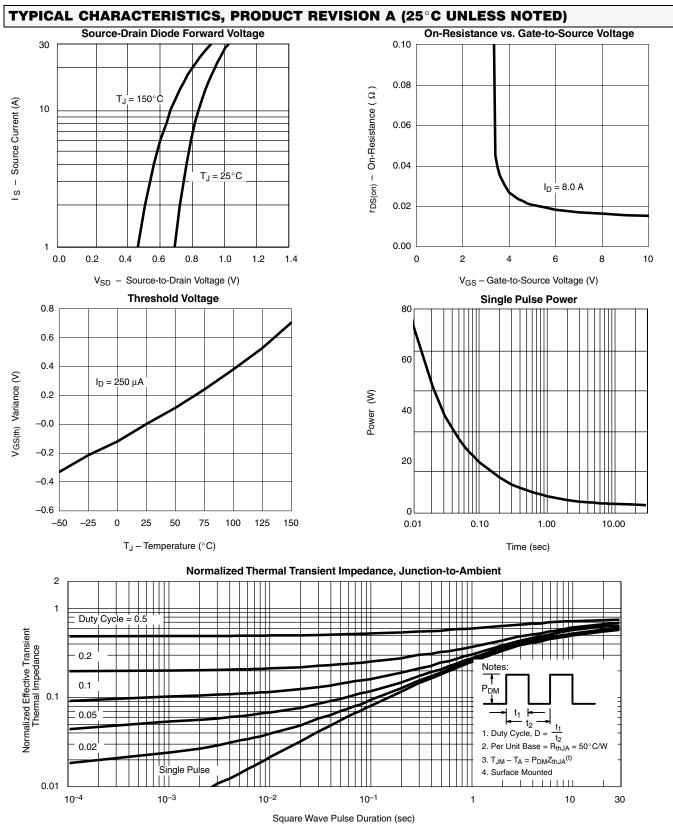


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### Si4435DY

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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?70149">http://www.vishay.com/ppg?70149</a>.



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1